



60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	$50m\Omega @ V_{GS} = 10V$	24A
60 V	$65m\Omega$ @ $V_{GS} = 4.5V$	21A

Features and Benefits

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching—Ensures More Reliable and Robust End Application
- Low R_{DS(ON)}—Minimizes Power Losses
- Low Q_G—Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

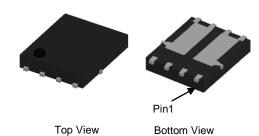
Description and Applications

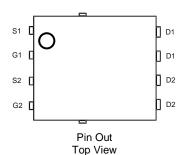
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

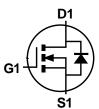
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

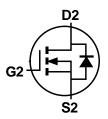
Mechanical Data

- Case: PowerDI[®]5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.097 grams (Approximate)









Equivalent Circuit

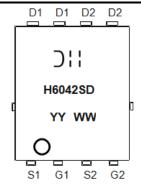
Ordering Information (Note 5)

Part Number	Case	Packaging
DMNH6042SPDQ-13	PowerDI5060-8 (Type C)	2500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



⊃¦¦ = Manufacturer's Marking H6042SD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018) WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	60	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	5.7 4.6	А
Continuous Drain Current (Note 8) V _{GS} = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	24 17	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	32	Α		
Maximum Continuous Body Diode Forward Current (Is	24	Α		
Avalanche Current (Note 9) L = 10mH	I _{AS}	3.5	Α		
Avalanche Energy (Note 9) L = 10mH			Eas	65	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)		P _D	1.2	W
Thermal Decistores, Juneties to Ambient (Note 6)		_	105	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	R _{ÐJA}	54	C/VV
Total Power Dissipation (Note 7)		P _D	2.5	W
The armed Bosistones, Junetics to Ambient (Note 7)		D	51	
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	R _{ÐJA}	26	°C/W
Thermal Resistance, Junction to Case (Note 8)	Rejc	3.5		
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +175	°C	

Notes:

- 6. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
- 7. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

 8. Thermal resistance from junction to soldering point (on the exposed drain pad).

 9. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.



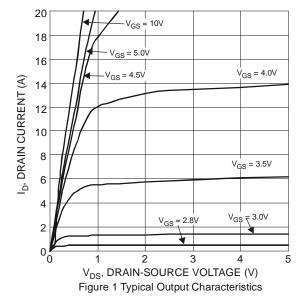
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

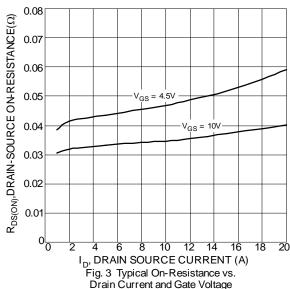
Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage		60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C		_	_	1	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	V _{GS(TH)}	1.0		3.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	D	_	34	50	mΩ	$V_{GS} = 10V, I_D = 5.1A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	45	65	11122	$V_{GS} = 4.5V, I_D = 4.4A$	
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 2.6A$	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	CISS	_	584	_	pF	V _{DS} = 25V, V _{GS} = 0V, -f = 1.0MHz	
Output Capacitance	Coss	_	83	_	pF		
Reverse Transfer Capacitance	C _{RSS}		24	_	pF		
Gate Resistance	Rg	_	3.8	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q _G	_	4.2	_	nC		
Total Gate Charge (V _{GS} = 10V)	Q _G	_	8.8	_	nC	1, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	
Gate-Source Charge	Q _{GS}	_	1.8	_	nC	$V_{DS} = 44V, I_{D} = 5.2A$	
Gate-Drain Charge	Q_{GD}	_	1.8	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	3.4	_	ns		
Turn-On Rise Time	t _R	_	1.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_G = 6\Omega, I_D = 1A$	
Turn-Off Delay Time	t _{D(OFF)}	I	10.1	_	ns		
Turn-Off Fall Time	t _F	1	4.5	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	1	12.9	_	ns	$I_F = 2.6A$, $di/dt = 100A/\mu s$	
Body Diode Reverse Recovery Charge		1	5.4	_	nC	$I_F = 2.6A$, $di/dt = 100A/\mu s$	

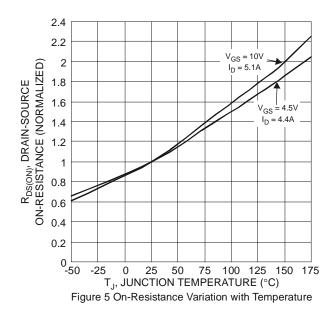
Notes:

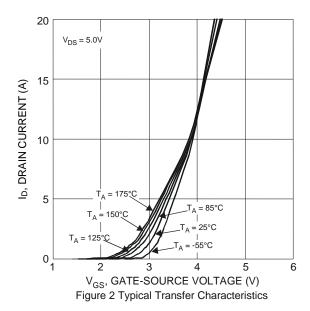
Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.











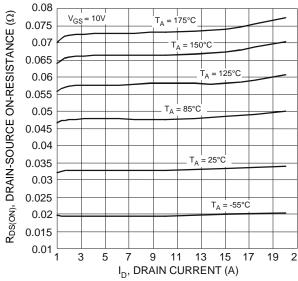


Figure 4 Typical On-Resistance vs.
Drain Current and Temperature

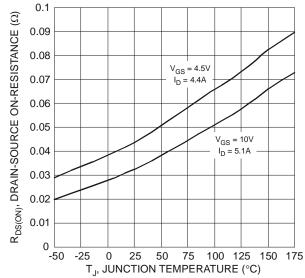


Figure 6 On-Resistance Variation with Temperature



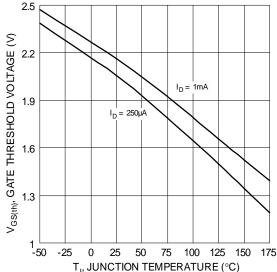


Figure 7 Gate Threshold Variation vs. Junction Temperature

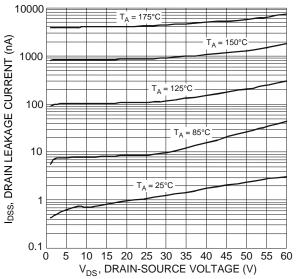


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

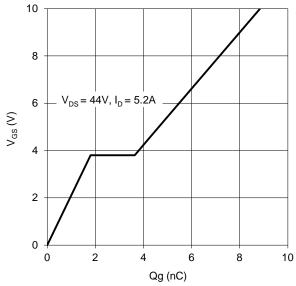


Figure 11 Gate Charge

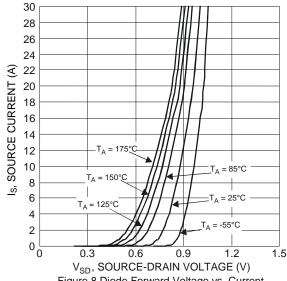
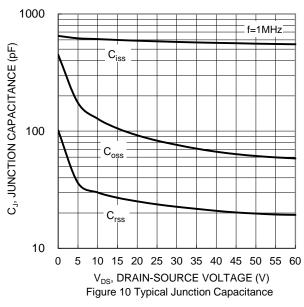


Figure 8 Diode Forward Voltage vs. Current



100
R_{DS(on)}
Limited

10
R_{DS(on)}
Limited

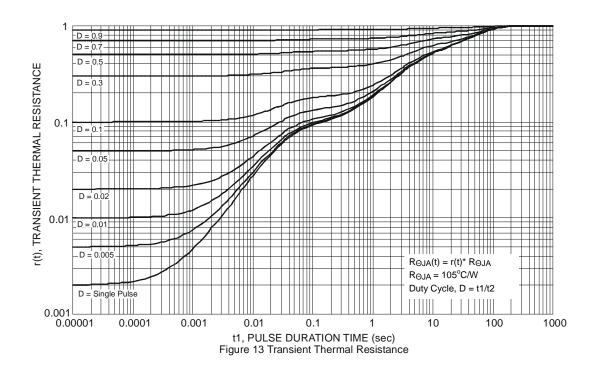
10
R_{DS(on)}
Limited

10
R_{DS(on)}
Limited

10
R_{DS(on)}
R_{DS(on)}
Limited

10
R_{DS(on)}
R



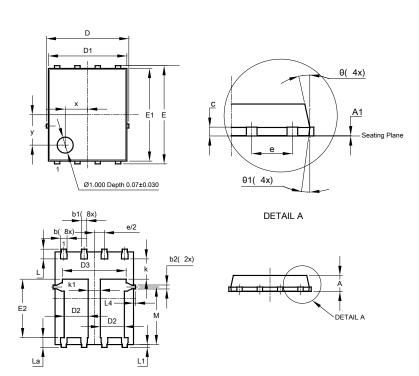




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)



PowerDI5060-8 (Type C)						
Dim	Min	Min Max Typ				
Α	0.90	1.10	1.00			
A1	0	0.05	0.02			
b	0.33	0.51	0.41			
b1	0.300	0.366	0.333			
b2	0.20	0.35	0.25			
C	0.23	0.33	0.277			
D	5	.15 BSC				
D1	4.85	4.95	4.90			
D2	1.40	1.60	1.50			
D3		_	3.98			
E	6	6.15 BSC				
E1	5.75	5.85	5.80			
E2	3.56	3.76	3.66			
е	1.27BSC					
k			1.27			
k1	0.56	_	-			
L	0.51	0.71	0.61			
La	0.51	0.71	0.61			
L1	0.05 0.20 0.175					
L4	— — 0.12					
М	3.50	3.71 3.60				
х		— — 1.400				
у	_	_	1.900			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	3.910			
X2	1.650			
Х3	1.650			
X4	4.420			
Y	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			



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